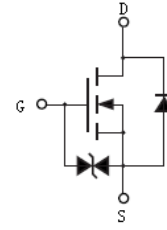


Features

- Low power loss by high speed switching and low on-resistance
- Excellent thermal behavior
- Very low FOM for fast switching efficiency
- Product validation acc. JEDEC Standard
- Integrated ESD protection diode: HBM: JESD22-A114-B: 2
- RoHS compliant with Halogen-free

HF

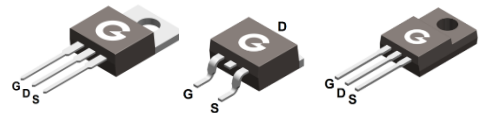


Applications

- LED lighting
- Adapters
- Chargers
- Industrial power
- PFC stage

Mechanical Data

- Case: TO-220AB, TO-263, ITO-220AB
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



TO-220AB TO-263 ITO-220AB

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
SJM80R680	TO-220AB	50 pcs / Tube	SJM80R680
SJM80R680B	TO-263	50 pcs / Tube or 800 pcs / Tape & Reel	SJM80R680B
SJM80R680F	ITO-220AB	50 pcs / Tube	SJM80R680F

Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	800	V
Gate-to-Source Voltage (Static)	V_{GSS}	± 20	V
Continuous Drain Current ($T_C = 25^\circ\text{C}$)	I_D	8	A
Continuous Drain Current ($T_C = 100^\circ\text{C}$)		5	A
Pulsed Drain Current ($t_p = 10\mu\text{s}$, $T_C = 25^\circ\text{C}$)	I_{DM}	32	A
Single Pulse Avalanche Energy ²	E_{AS}	160	mJ
Power Dissipation (TO-220AB, $T_C = 25^\circ\text{C}$)	P_D	83	W
Power Dissipation (TO-263, $T_C = 25^\circ\text{C}$)		83	W
Power Dissipation (ITO-220AB, $T_C = 25^\circ\text{C}$)		31	W
Operating Junction Temperature Range	T_J	-55 ~ +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case (TO-220AB, TO-263)	R _{θJC}	-	1.2	1.5	°C/W
Thermal Resistance Junction-to-Case (ITO-220AB)		-	3.6	4	°C/W
Thermal Resistance Junction-to-Air (TO-220AB, TO-263)	R _{θJA}	-	-	62	°C/W
Thermal Resistance Junction-to-Air (ITO-220AB)		-	-	75	°C/W

Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	800	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 800V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	-	-	±1	μA
On Characteristics						
R _{DS(ON)}	Drain-Source On-resistance *1	V _{GS} = 10V, I _D = 2A	-	0.54	0.68	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	3.3	4	V
R _G	Gate Resistance	V _{GS} = 0V, f = 1MHz	-	6.8	-	Ω
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V V _{DS} = 40V f = 250kHz	-	748	-	pF
C _{OSS}	Output Capacitance		-	66	-	
C _{RSS}	Reverse Transfer Capacitance		-	2.8	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time	V _{DD} = 400V V _{GS} = 15V I _D = 4A R _G = 3.3Ω	-	47	-	ns
t _r	Turn-on Rise Time		-	36	-	
t _{d(OFF)}	Turn-Off Delay Time		-	96	-	
t _f	Turn-Off Fall Time		-	70	-	
Q _G	Total Gate-Charge	V _{DD} = 640V V _{GS} = 10V I _D = 4A	-	21.1	-	nC
Q _{GS}	Gate to Source Charge		-	3	-	
Q _{GD}	Gate to Drain (Miller) Charge		-	9.2	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *1	I _{SD} = 4A, V _{GS} = 0V	-	0.85	1.3	V
t _{rr}	Reverse Recovery Time	I _F = 4A, V _R = 400V	-	305	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt = 100A/μs	-	2.7	-	μC

Notes:

- The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%
- The E_{AS} data shows Max. rating. The test condition is V_{DD} = 100V, V_{GS} = 10V, L = 50mH

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

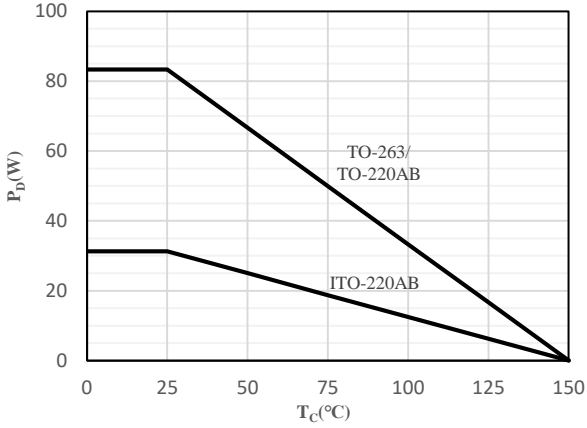


Fig 1 Power Dissipation

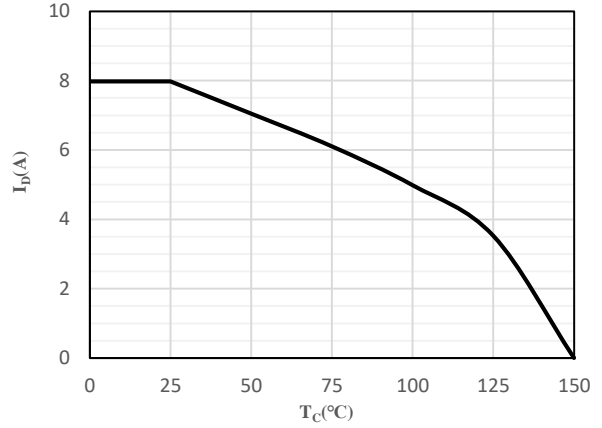


Fig 2 Drain Current

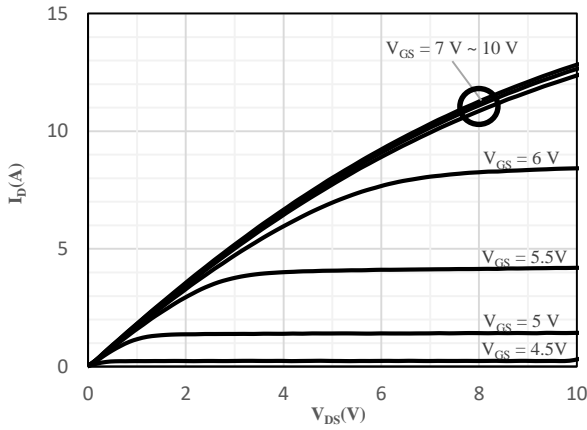


Fig 3 Typical Output Characteristics

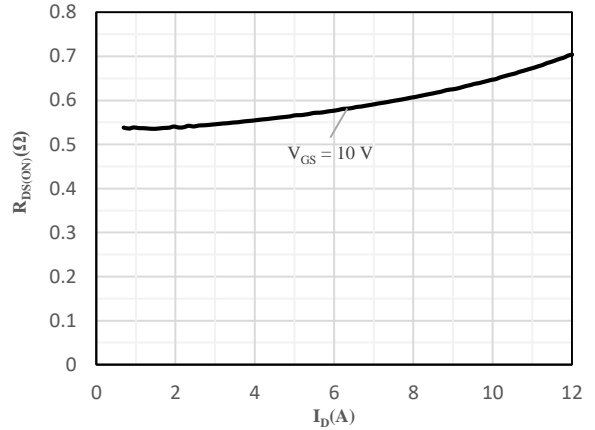


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

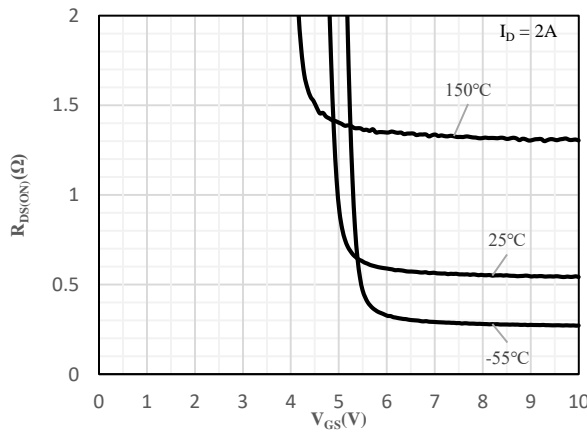


Fig 5 On-Resistance vs. Gate-Source Voltage

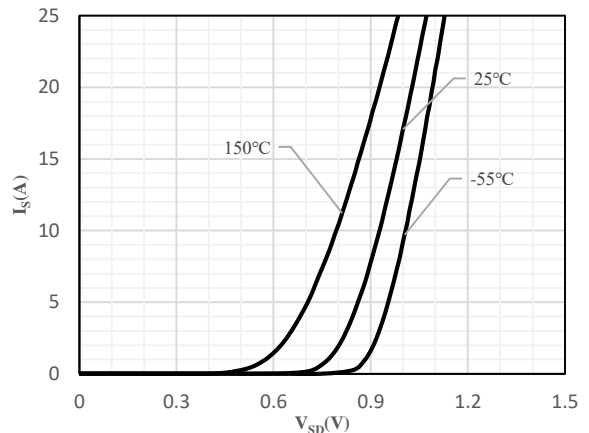


Fig 6 Body-Diode Characteristics

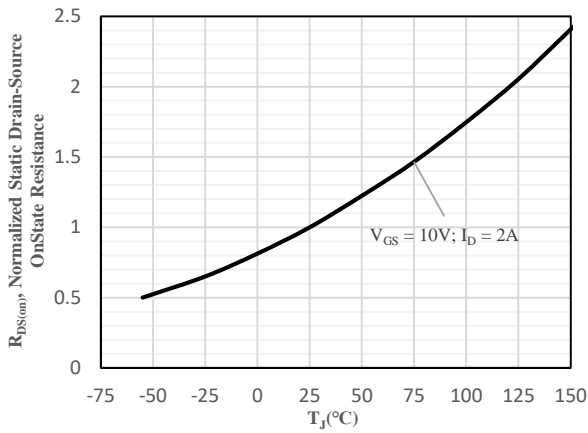


Fig 7 Normalized On-Resistance vs. Junction Temperature

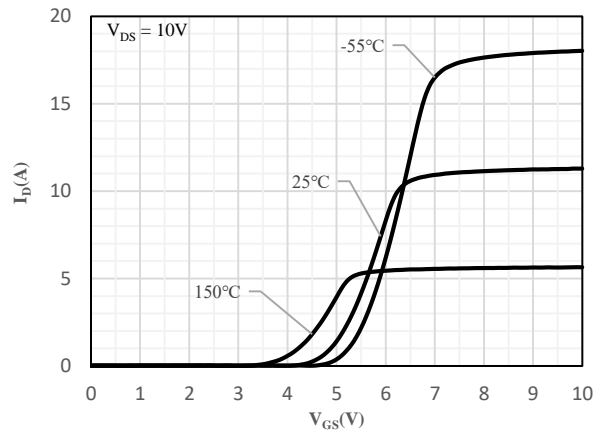


Fig 8 Transfer Characteristics

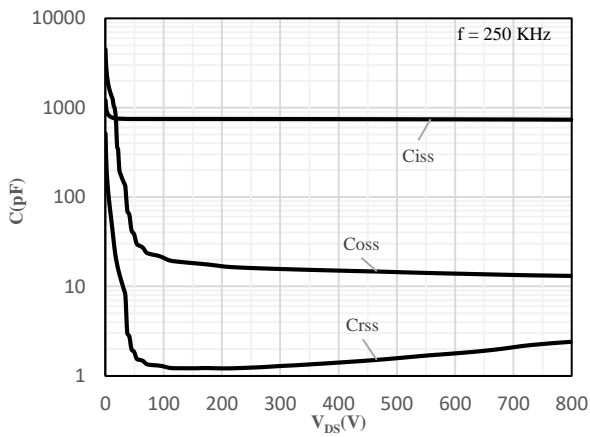


Fig 9 Capacitance Characteristics

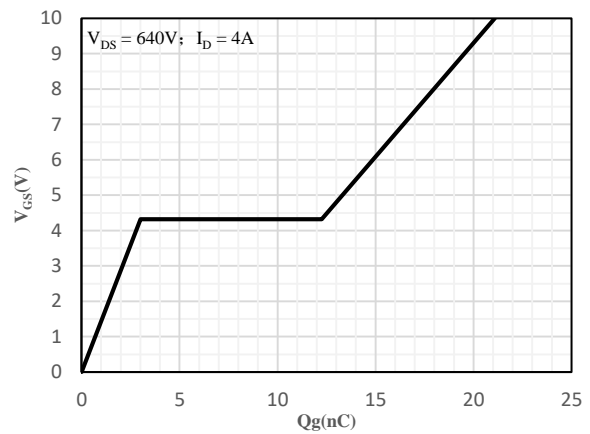


Fig 10 Gate-Charge Characteristics

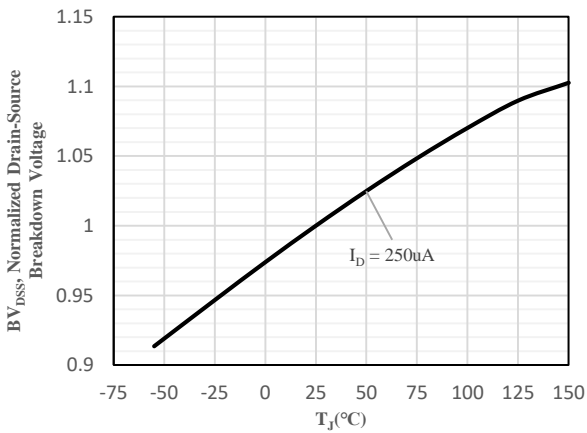


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

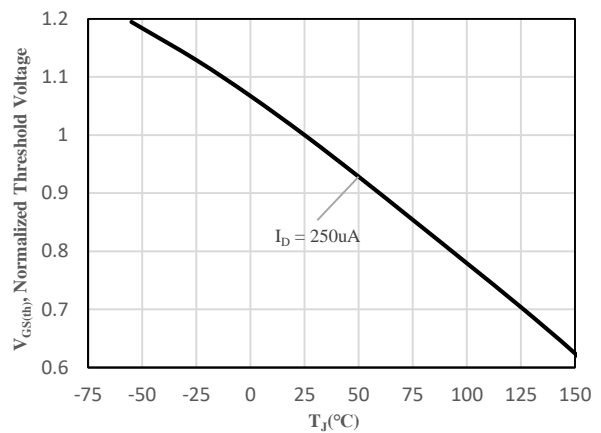


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

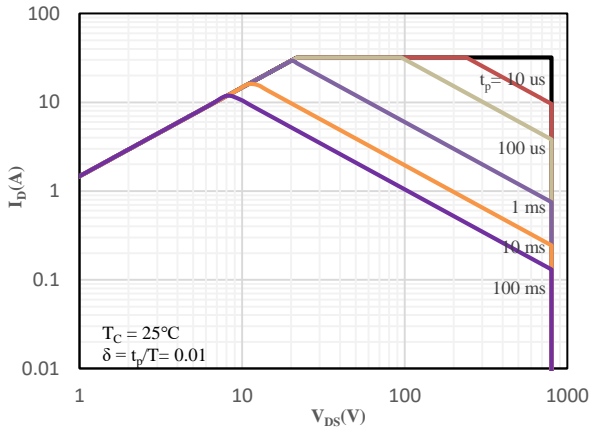


Fig 13 Safe Operating Area (TO-220AB / TO-263)

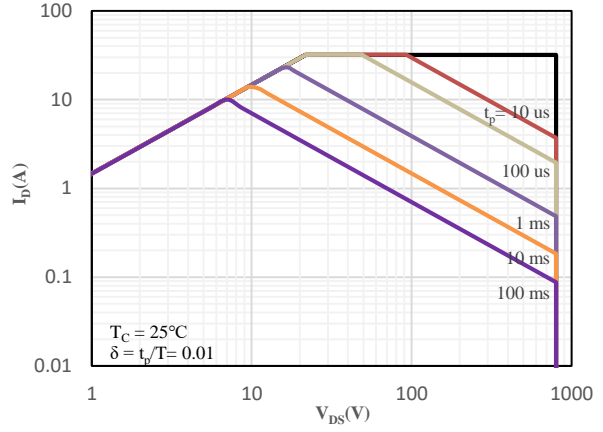


Fig 14 Safe Operating Area (ITO-220AB)

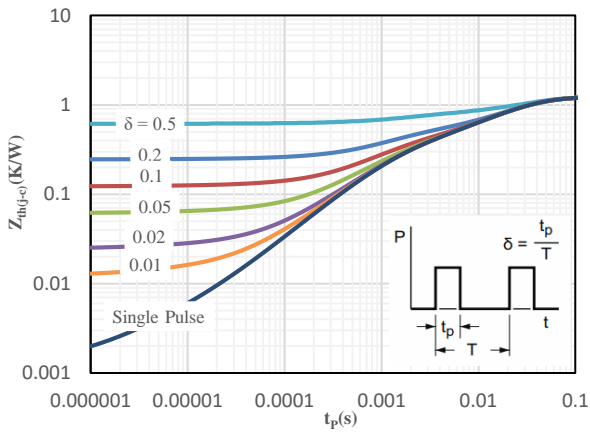


Fig 15 Maximum transient thermal impedance (TO-220AB / TO-263)

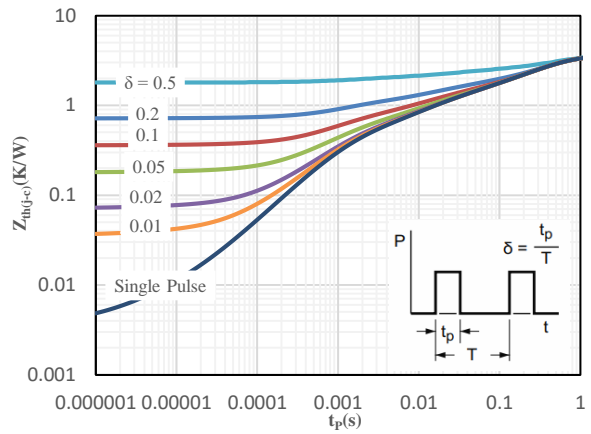
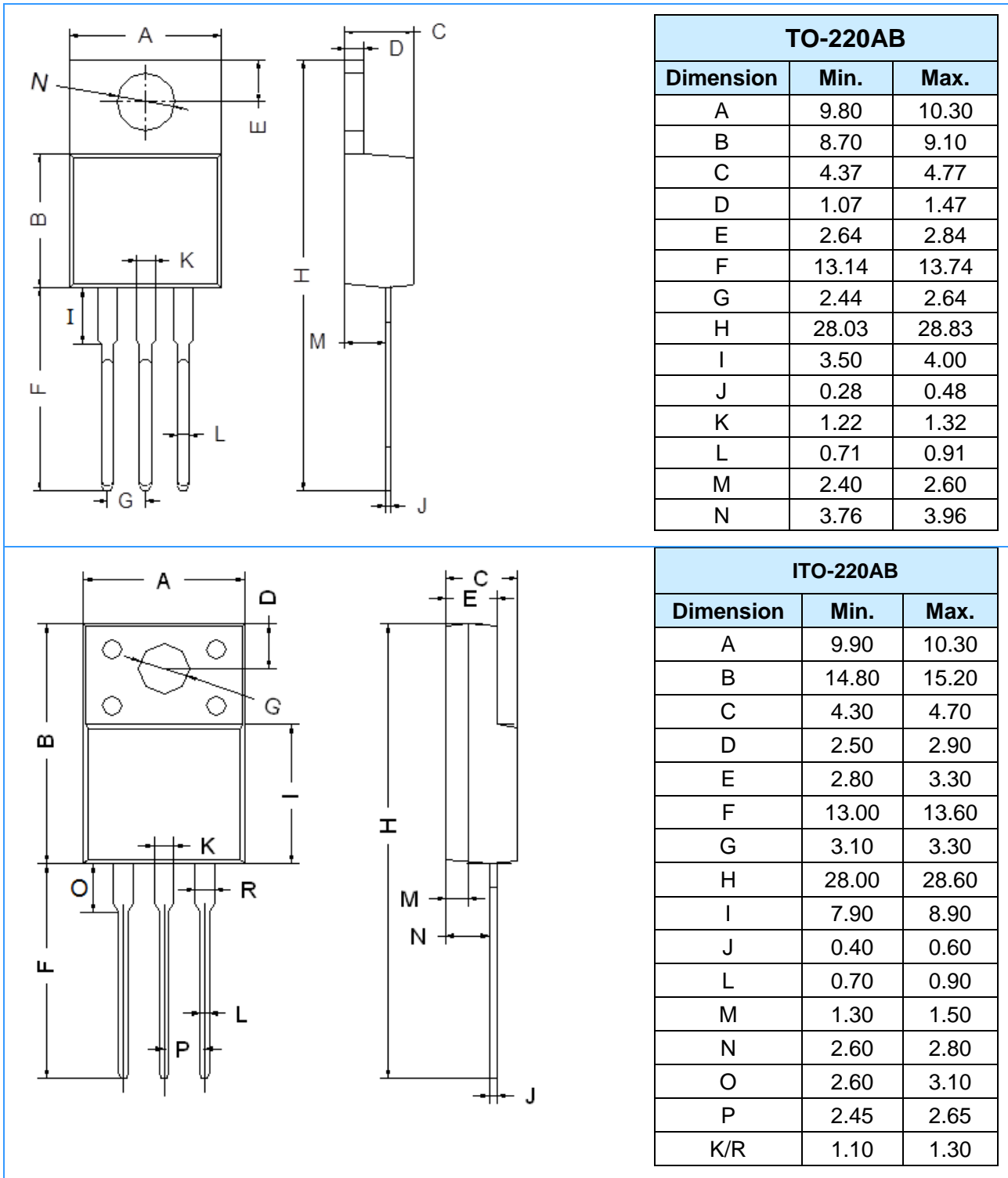
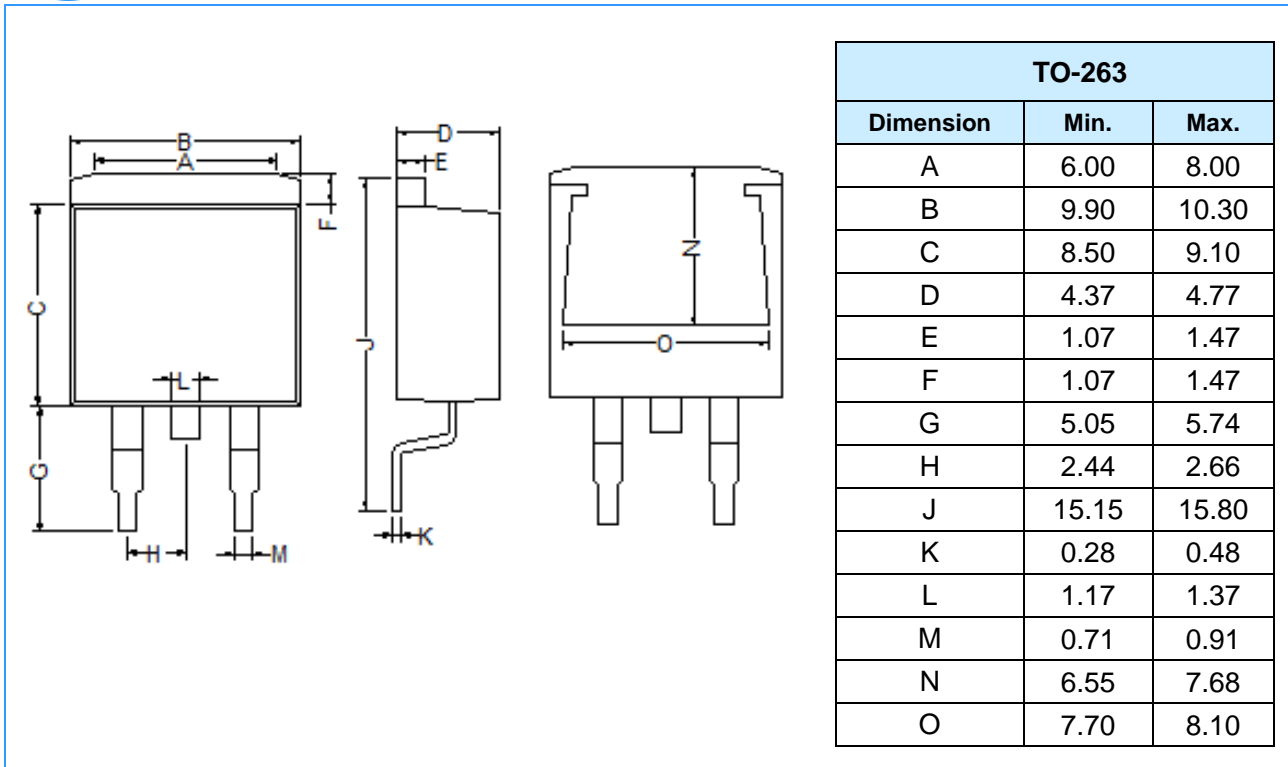


Fig 16 Maximum transient thermal impedance (ITO-220AB)

Package Outline Dimensions (Unit: mm)





Mounting Pad Layout (Unit: mm)

